AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph beginning on page 14 at line 21 to read as follows:

FIG. 4 shows a detailed structure of the p-type InGaN external base layer 8 regrown in the present embodiment. On the p-type InGaN base layer 2 exposed by etching, a 100 nm thick p-type InGaN layer 17 with the In mole fraction of 20% was regrown, followed by growing a thin p-type InGaN layer 13 with a thickness of 2 nm and the In mole fraction of 30%. The Mg concentration contained in the regrown p-type InGaN layers is 4×10^{19} cm^{-3}. In the present example, between the thin p-type InGaN layer 13 whose In mole fraction is 30% and the p-type InGaN layer ~~12~~ 17 whose In mole fraction 20%, polarization charge 14 occurs because of the distortion of crystals. The nitride semiconductor is characterized by having large polarization charge. In contrast, GaAs-based or InP-based compound semiconductors have only negligible polarization charge. When the InGaN with a higher In mole fraction is grown on the InGaN with a lower In mole fraction, negative polarization charge takes place at the interface. Utilizing the property makes it possible to reduce the contact resistance between the p-type nitride semiconductor and a metal (see, Japanese patent application laid-open No. 2003-007998 "low-resistance nitride semiconductor and its fabrication method" by Kumakura, Makimoto and Kobayashi, for example, or non-patent document 6: K. Kumakura, T. Makimoto and N. Kobayashi, Applied Physics Letters, Vol. 79, No. 16, pp.2588 - 2590 (2001)).

Please amend the paragraph beginning on page 18 at line 2 to read as follows:

A conventional HBT was fabricated through a typical HBT process of FIG. 9 without applying the present invention. FIG. ~~5~~6 illustrates an example of the common emitter I-V characteristics introduced in the non-patent document 2. The HBT, which employs the p-type InGaN layer as the base layer, has lesser process damage than the HBT using the p-type GaN. Nevertheless, the maximum value of the current gain is about 20, and the offset voltage is about 6 V. The deviation of the offset voltage from the expected value is not less than 5 V.

Please replace the Abstract with the following amended Abstract:

A nitride semiconductor structure is provided which greatly improves ohmic characteristics by repairing process damage by regrowing an indium-containing p-type nitride semiconductor on a p-type nitride semiconductor having the process damage. In addition, a nitride semiconductor bipolar transistor is provided which can greatly improve its current gain and offset voltage. The structure includes an indium-containing p-type nitride semiconductor layer ~~(8)~~ on a p-type nitride semiconductor ~~(2)~~ processed by etching. The bipolar transistor, which has a base layer composed of a p-type nitride semiconductor, has an indium-containing p-type InGaN base layer ~~(8)~~ regrown on a surface of a p-type InGaN base layer ~~(2)~~ exposed by etching an emitter layer ~~(1)~~.